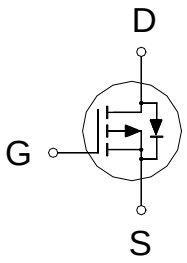
NIKO-SEM

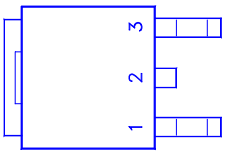
P-Channel Enhancement Mode Field Effect Transistor

PD537BA
TO-252
Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30V	8mΩ	-71A





1. GATE
2. DRAIN
3. SOURCE

RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current[2]	T_C = 25 °C	I_D	-71	A
	T_C = 100 °C		-45	
Pulsed Drain Current[1]		I_{DM}	-160	
Avalanche Current		I_{AS}	-36	
Avalanche Energy	L = 0.1mH	E_{AS}	64.8	mJ
Power Dissipation	T_C = 25 °C	P_D	73	W
	T_C = 100 °C		29	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		1.7	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.
[2]Package limitation current is -55A.

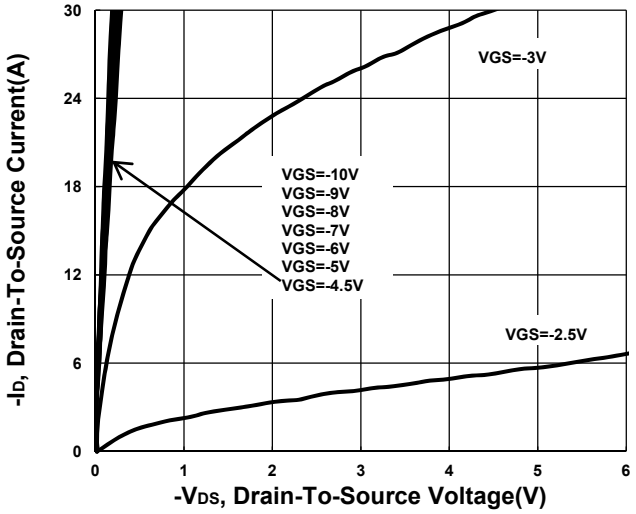
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.6	-3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±25V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24V, V_{GS} = 0V			-1	μA
		V_{DS} = -20V, V_{GS} = 0V, T_J = 125 °C			-10	

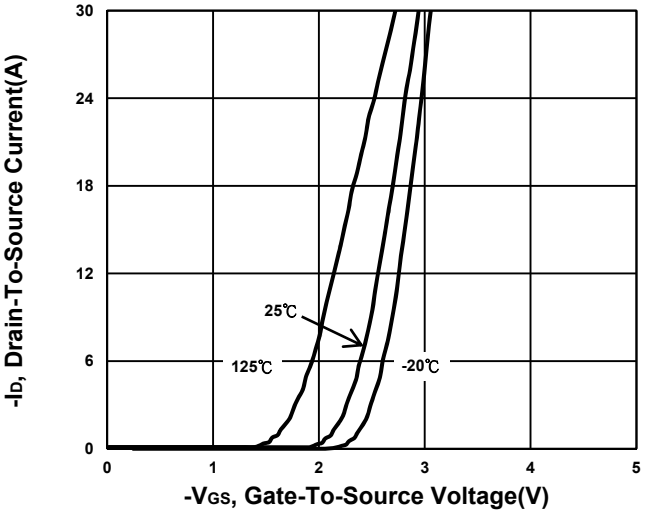
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = -10V, I_D = -20A		6.5	8	mΩ
		V_{GS} = -4.5V, I_D = -20A		9.6	14	
Forward Transconductance[1]	g_{fs}	V_{DS} = -5V, I_D = -20A		49		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1MHz		2464		pF
Output Capacitance	C_{oss}			374		
Reverse Transfer Capacitance	C_{rss}			271		
Gate Resistance	R_g	V_{GS} =0V, V_{DS} = 0V, f = 1MHz		3.8		Ω
Total Gate Charge[2]	Q_g (V_{GS}=-10V)	V_{DS} = -15V , I_D = -20A		55		nC
	Q_g(V_{GS}=-4.5V)			27		
Gate-Source Charge[2]	Q_{gs}			8.3		
Gate-Drain Charge[2]	Q_{gd}			11		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = -15V , I_D ≅ -20A, V_{GS} = -10V, R_{GEN} =6Ω		15		nS
Rise Time[2]	t_r			20		
Turn-Off Delay Time[2]	$t_{d(off)}$			41		
Fall Time[2]	t_f			23		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				-56	A
Forward Voltage[1]	V_{SD}	I_F = -20A, V_{GS} = 0V			-1.3	V
Reverse Recovery Time	t_{rr}	I_F = -20A, dI_F/dt = 100A / μS		26		nS
Reverse Recovery Charge	Q_{rr}			13		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.
[3]Package limitation current is -55A.

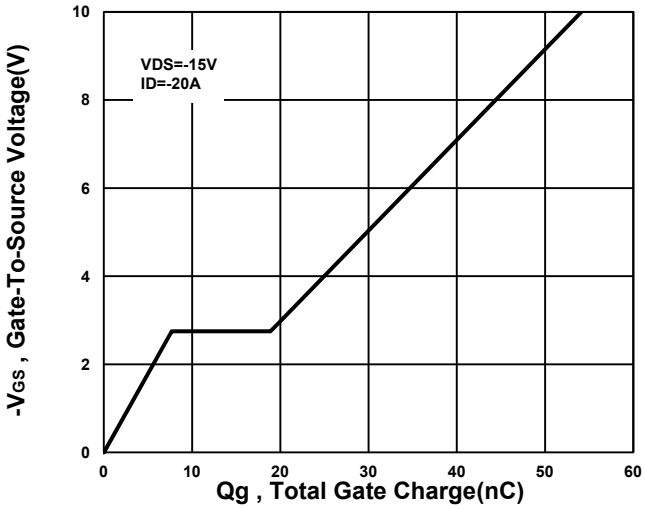
Output Characteristics



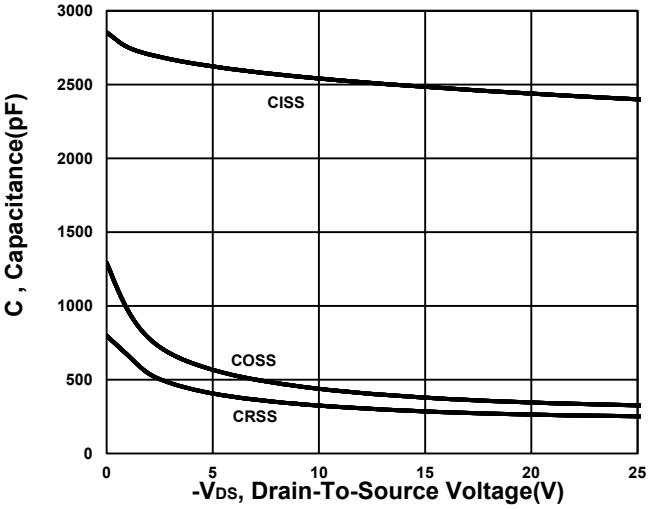
Transfer Characteristics



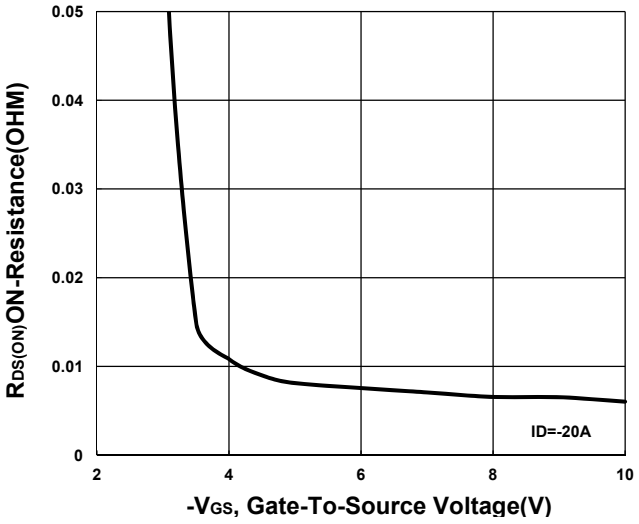
Gate charge Characteristics



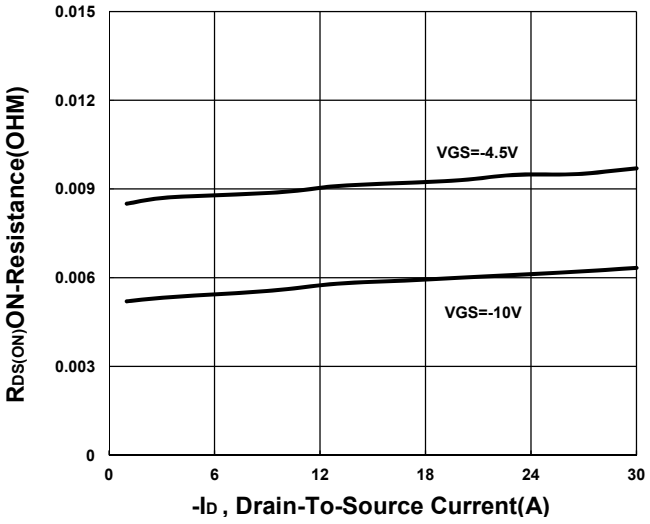
Capacitance Characteristic



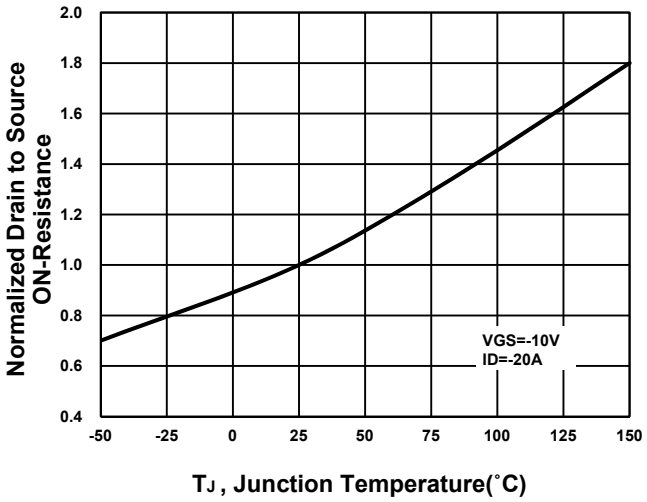
On-Resistance VS Gate-To-Source



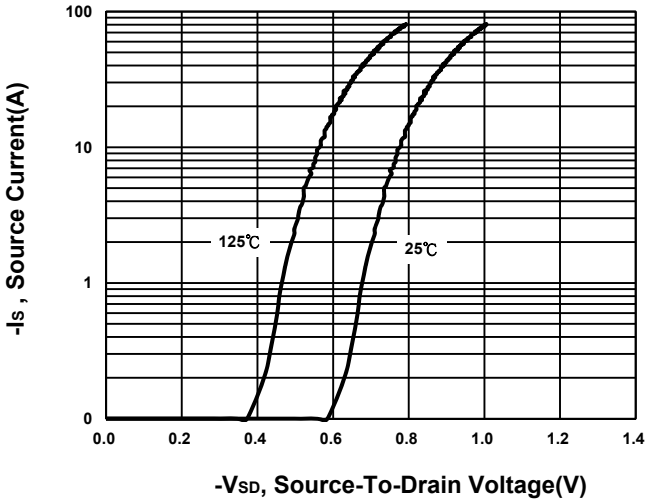
On-Resistance VS Drain Current



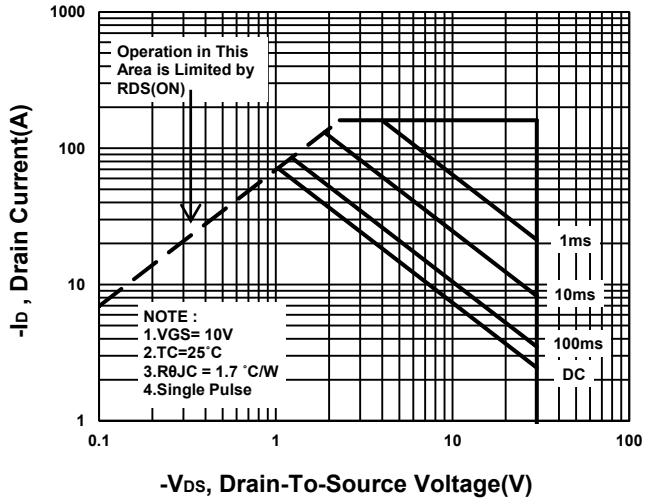
On-Resistance VS Temperature



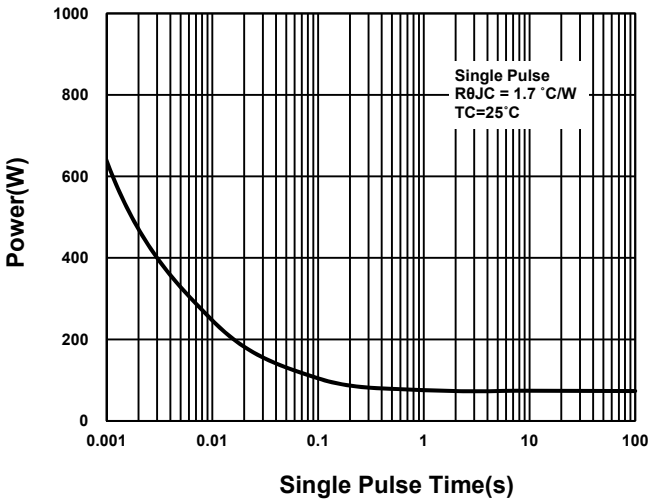
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve